

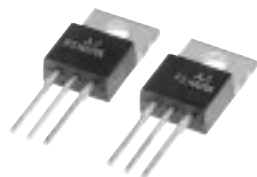
PRELIMINARY
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MITSUBISHI Nch POWER MOSFET

FS10UMA-5A

HIGH-SPEED SWITCHING USE

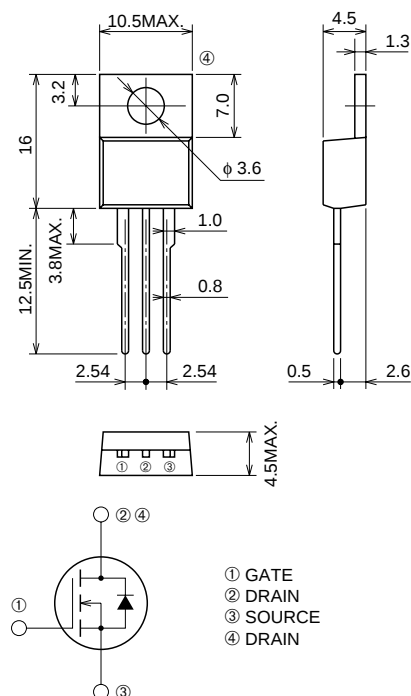
FS10UMA-5A



- 10V DRIVE
- V_{DS} 250V
- $r_{DS(ON)}$ (MAX) 0.52Ω
- I_D 10A

OUTLINE DRAWING

Dimensions in mm



TO-220

APPLICATION

Cs Switch for CRT Display monitor

MAXIMUM RATINGS (Tc = 25°C)

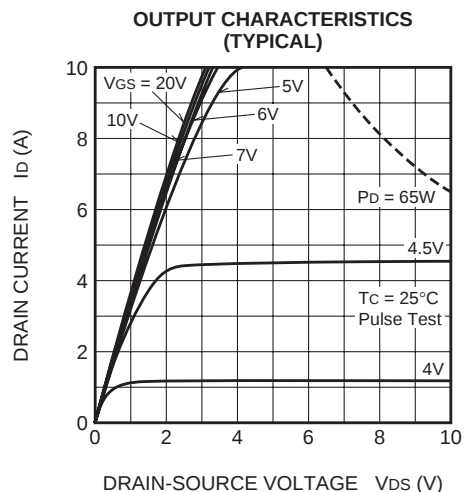
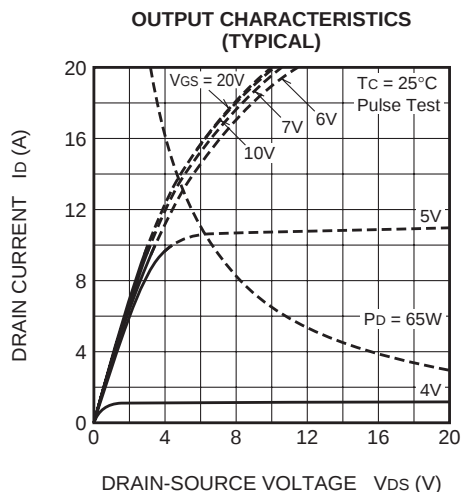
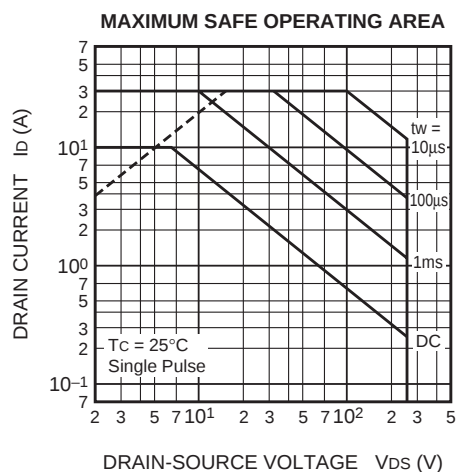
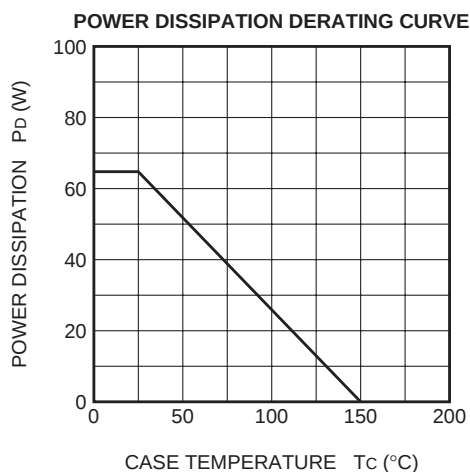
Symbol	Parameter	Conditions	Ratings	Unit
V_{DS}	Drain-source voltage	$V_{GS} = 0V$	250	V
V_{GS}	Gate-source voltage	$V_{DS} = 0V$	± 20	V
I_D	Drain current		10	A
I_{DM}	Drain current (Pulsed)		30	A
I_{DA}	Avalanche current (Pulsed)	$L = 200\mu H$	10	A
P_D	Maximum power dissipation		65	W
T_{ch}	Channel temperature		$-55 \sim +150$	°C
T_{stg}	Storage temperature		$-55 \sim +150$	°C
—	Weight	Typical value	2.0	g

Jan. 2000

ELECTRICAL CHARACTERISTICS ($T_{ch} = 25^{\circ}\text{C}$)

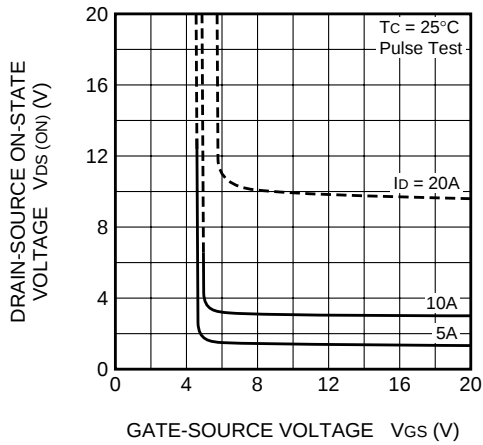
Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{mA}$, $V_{GS} = 0\text{V}$	250	—	—	V
I_{GSS}	Gate-source leakage current	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$	—	—	± 0.1	μA
I_{DSS}	Drain-source leakage current	$V_{DS} = 250\text{V}$, $V_{GS} = 0\text{V}$	—	—	1	mA
$V_{GS(th)}$	Gate-source threshold voltage	$I_D = 1\text{mA}$, $V_{DS} = 10\text{V}$	2.0	3.0	4.0	V
$r_{DS(on)}$	Drain-source on-state resistance	$I_D = 5\text{A}$, $V_{GS} = 10\text{V}$	—	0.40	0.52	Ω
$V_{DS(on)}$	Drain-source on-state voltage	$I_D = 5\text{A}$, $V_{GS} = 10\text{V}$	—	2.00	2.60	V
$ y_{fs} $	Forward transfer admittance	$I_D = 5\text{A}$, $V_{DS} = 10\text{V}$	—	9.0	—	S
C_{iss}	Input capacitance	$V_{DS} = 25\text{V}$, $V_{GS} = 0\text{V}$, $f = 1\text{MHz}$	—	950	—	pF
C_{oss}	Output capacitance		—	90	—	pF
C_{rss}	Reverse transfer capacitance		—	25	—	pF
$t_d(on)$	Turn-on delay time	$V_{DD} = 150\text{V}$, $I_D = 5\text{A}$, $V_{GS} = 10\text{V}$, $R_{GEN} = R_{GS} = 50\Omega$	—	20	—	ns
t_r	Rise time		—	25	—	ns
$t_d(off)$	Turn-off delay time		—	150	—	ns
t_f	Fall time		—	40	—	ns
V_{SD}	Source-drain voltage	$I_S = 5\text{A}$, $V_{GS} = 0\text{V}$	—	1.5	2.0	V
$R_{th(ch-c)}$	Thermal resistance	Channel to case	—	—	1.92	$^{\circ}\text{C/W}$

PERFORMANCE CURVES

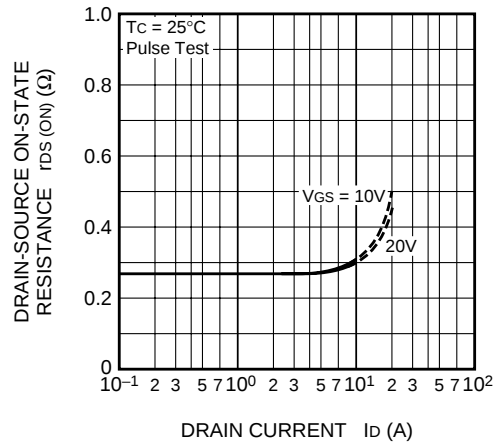


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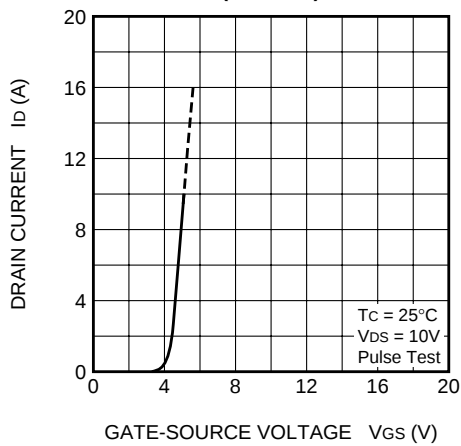
ON-STATE VOLTAGE VS. GATE-SOURCE VOLTAGE (TYPICAL)



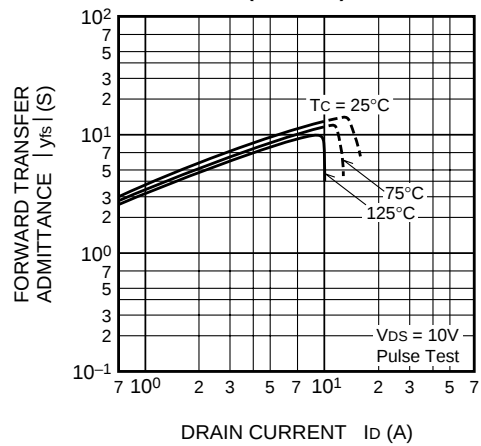
ON-STATE RESISTANCE VS. DRAIN CURRENT (TYPICAL)



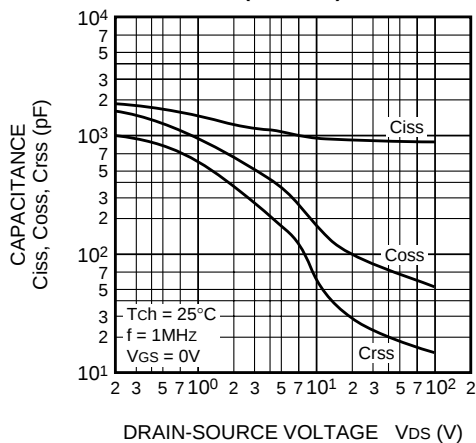
TRANSFER CHARACTERISTICS (TYPICAL)



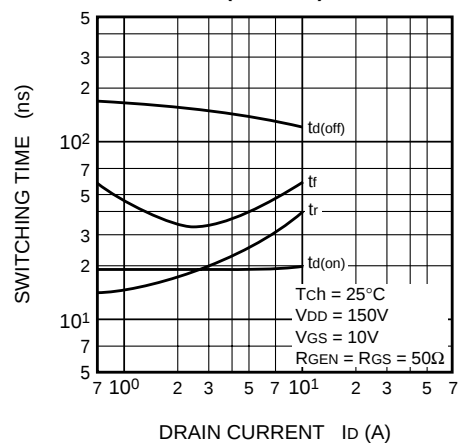
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT (TYPICAL)



CAPACITANCE VS. DRAIN-SOURCE VOLTAGE (TYPICAL)

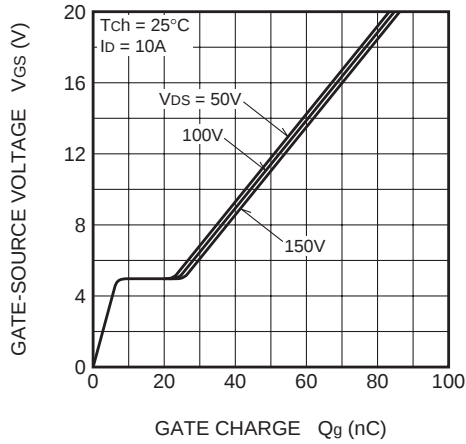


SWITCHING CHARACTERISTICS (TYPICAL)

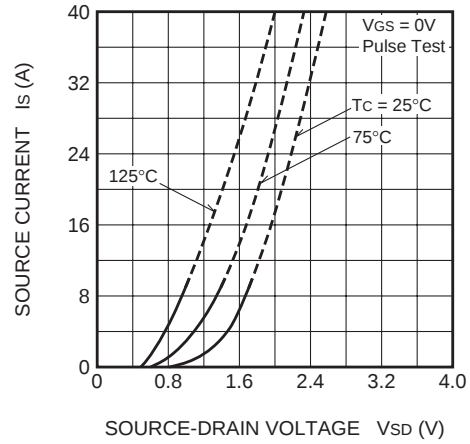


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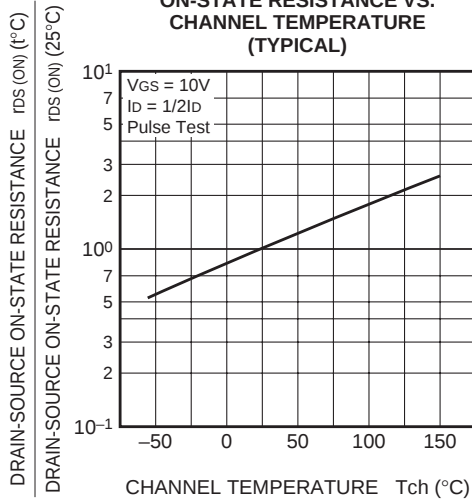
**GATE-SOURCE VOLTAGE
 VS. GATE CHARGE
 (TYPICAL)**



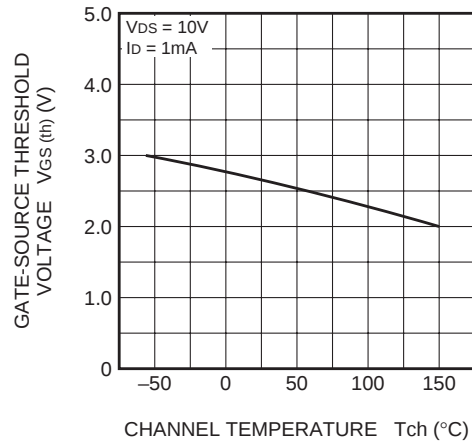
**SOURCE-DRAIN DIODE
 FORWARD CHARACTERISTICS
 (TYPICAL)**



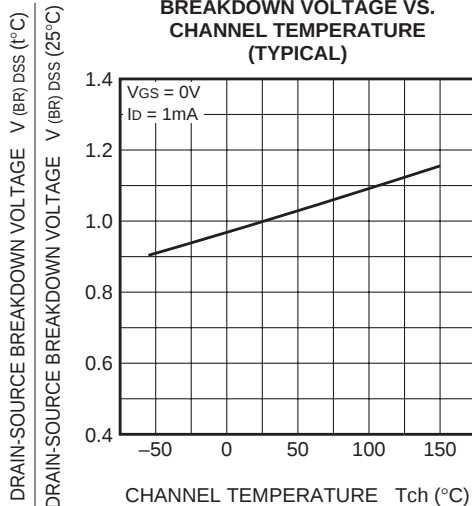
**ON-STATE RESISTANCE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**THRESHOLD VOLTAGE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**BREAKDOWN VOLTAGE VS.
 CHANNEL TEMPERATURE
 (TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE
 CHARACTERISTICS**

